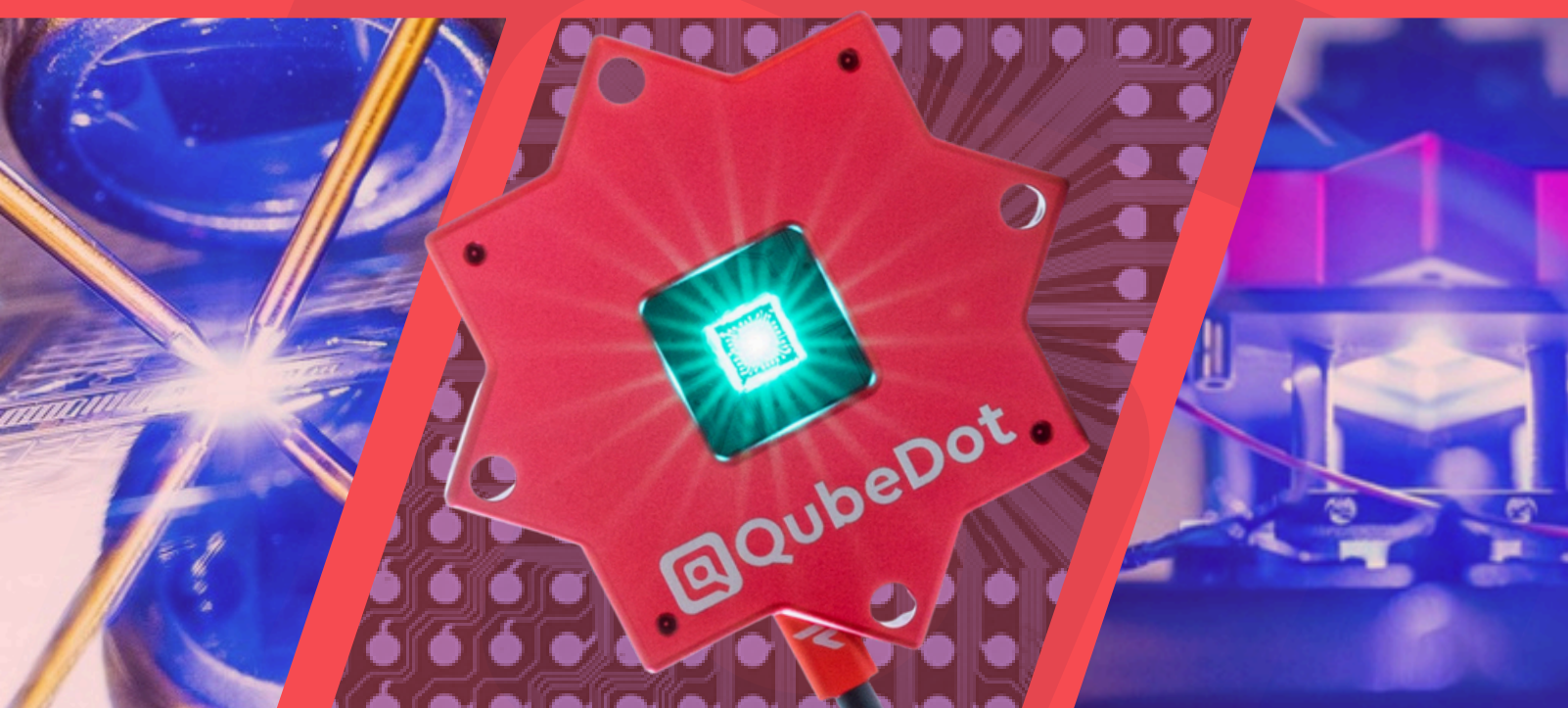
Made in

Optical Interconnect as a Service

GaN Emitter Processing and High-Frequency Characterization



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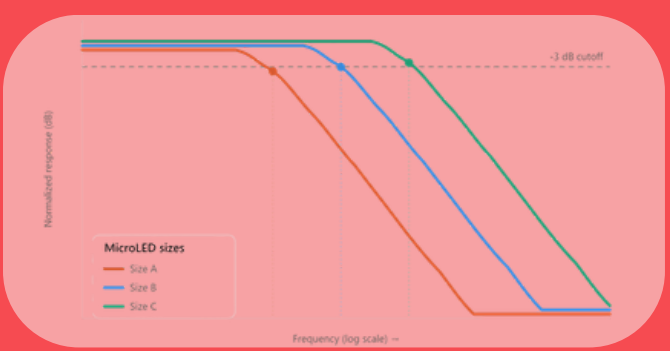
Your epitaxy, our cleanroom. We turn GaN wafers into high-frequency microLED emitters and hand back measured data, not assumptions. Each emitter switches at up to 1 GHz. Can depend on your epitaxy, if you provide your own. Put the emitters in an array and you get parallel optical channels from a single chip, at a fraction of the energy per bit of a conventional source.

Key Specs

Modulation Speed	Up to 1 GHz per emitter
Minimum feature Size	Down to 1 µm
Wavelengths	450 or 530 nm or customized, depending on your own epitaxy
Wafer Size	4" and 6" and 8"
Minimum Batch	Wafer-level electro-optical mapping, IVL sweeps and IQE/EQE measurements, spectral 350 to 1000 nm. High speed measurements up to 1.4 GHz



Parallel Optical Channels

1 GHz Modulation

Process and Measure, One Place

High Frequency Material Characterization and Chip Supply

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Contact Us

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